

# GSM0976S

## 100V N-Channel MOSFETs

### Product Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

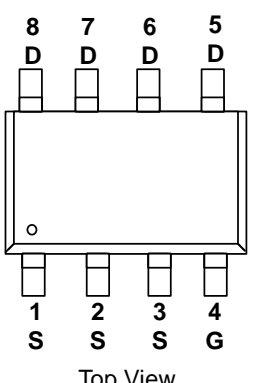
### Features

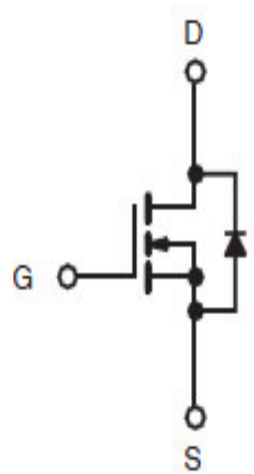
- 100V, 12A,  $R_{DS(ON)}=9.2m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### Applications

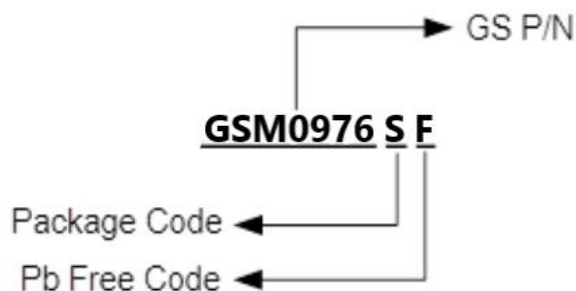
- Networking
- Load Switch
- LED Applications
- Quick Charger

### Packages & Pin Assignments

GSM0976SF (SOP-8)	
 <p>Top View</p>	
Pin	Description
1	Source
2	Source
3	Source
4	Gate
5	Drain
6	Drain
7	Drain
8	Drain

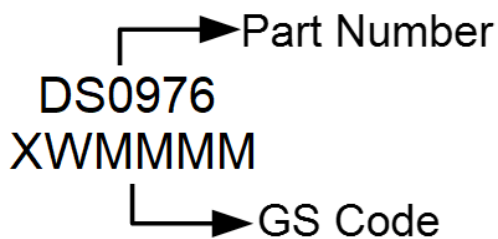


## Ordering Information



Part Number	Package	Quantity Reel
GSM0976SF	SOP-8	4000 PCS

## Marking Information



## Absolute Maximum Ratings

$T_C=25^\circ\text{C}$  Unless otherwise noted

Symbol	Parameter	Typical	Unit
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	$T_C=25^\circ\text{C}$	12
		$T_C=100^\circ\text{C}$	7.6
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	48	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	211	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	65	A
$P_D$	Power Dissipation ( $T_A=25^\circ\text{C}$ )	5	W
	Power Dissipation (Derate above $25^\circ\text{C}$ )	0.04	W/ $^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance-Junction to Case	25	$^\circ\text{C}/\text{W}$

Note 1: Repetitive Rating : Pulsed width limited by maximum junction temperature.

Note 2:  $V_{DD}=50\text{V}$ ,  $V_{GS}=10\text{V}$ ,  $L=0.1\text{mH}$ ,  $I_{AS}=65\text{A}$ ,  $R_G=25\ \Omega$ , Starting  $T_J=25^\circ\text{C}$ .

## Electrical Characteristics

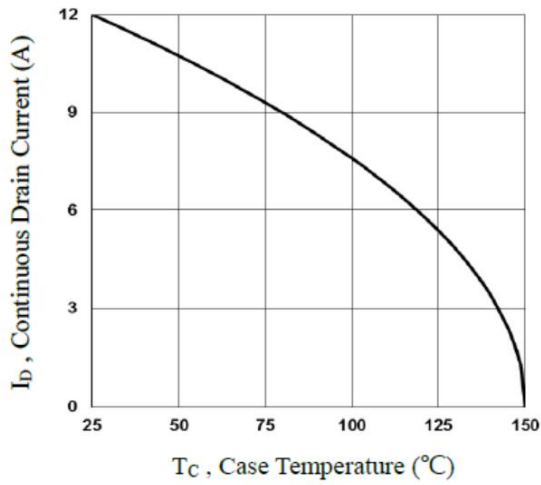
T<sub>J</sub>=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100			V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA		0.054		V/°C
V <sub>GS(th)</sub>	Gate Threshold Voltage		1.2	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA		-5.5		mV/°C
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C			10	
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current			12	A
I <sub>SM</sub>	Pulsed Source Current				24	
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =8.5A		7.6	9.2	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		10.8	14	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A		11		S
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A			1	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> =0V, I <sub>S</sub> =5A, di/dt=100A/us		47.6		ns
Q <sub>rr</sub>	Reverse Recovery Charge			68.3		nC
<b>Dynamic</b>						
Q <sub>g</sub>	Total Gate Charge <sup>3,4</sup>	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =8.5A		37.8	76	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3,4</sup>			7.8	16	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3,4</sup>			8.4	17	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz		2250	4500	pF
C <sub>oss</sub>	Output Capacitance			410	820	
C <sub>rss</sub>	Reverse Transfer Capacitance			25	50	
t <sub>d(on)</sub>	Turn-On Time <sup>3,4</sup>	V <sub>DD</sub> =50V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω		14.6	30	ns
t <sub>r</sub>				21.5	44	
t <sub>d(off)</sub>	Turn-Off Time <sup>3,4</sup>			54	108	
t <sub>f</sub>				84.3	168	
R <sub>g</sub>	Gate Resistance		V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz		1.43	

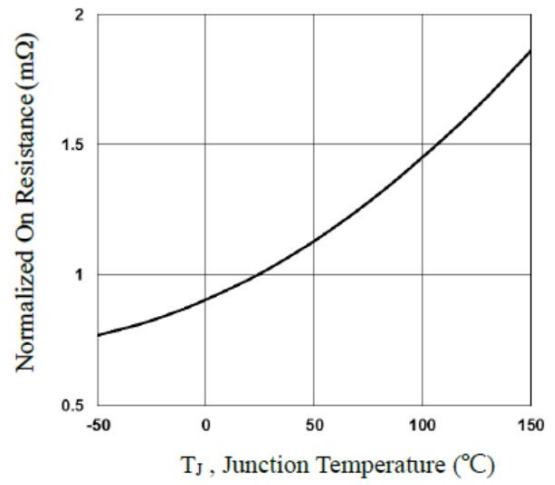
Note 3: The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.

Note 4: Essentially independent of operating temperature.

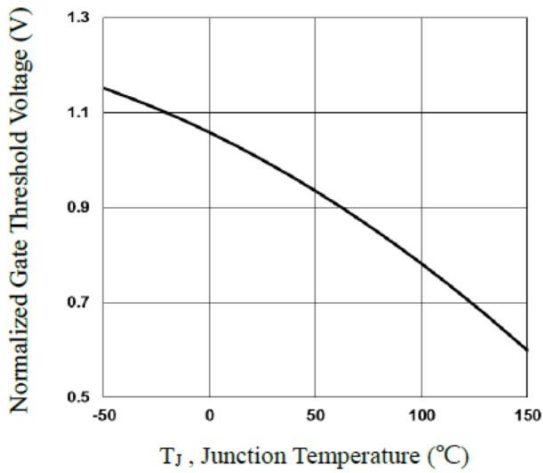
## Typical Performance Characteristics



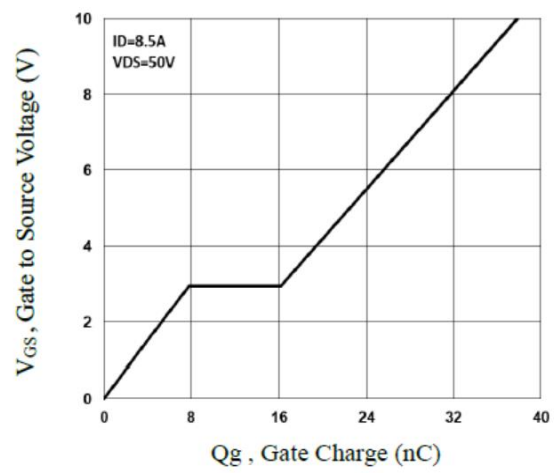
**Fig.1 Continuous Drain Current vs.  $T_C$**



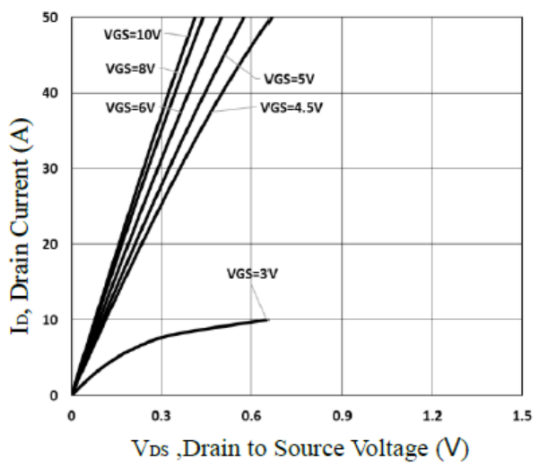
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$**



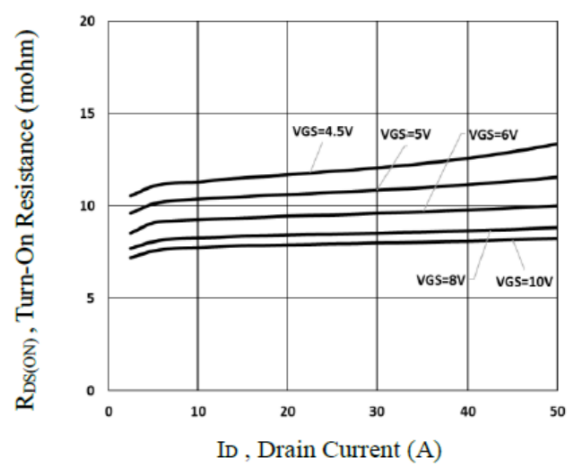
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



**Fig.4 Gate Charge Characteristics**

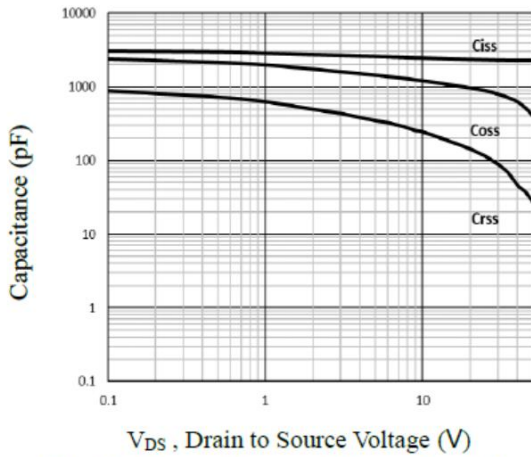


**Fig.5 Typical Output Characteristics**

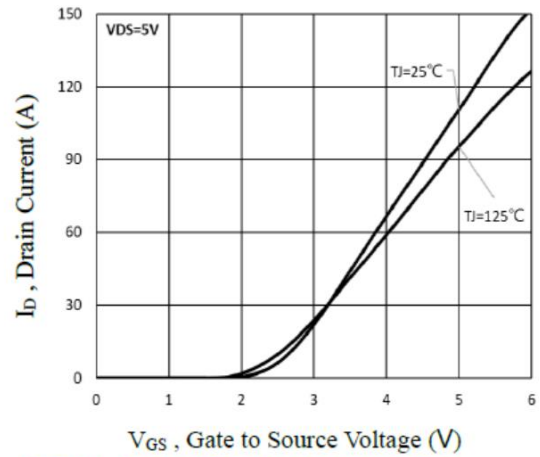


**Fig.6 Turn-On Resistance vs.  $I_D$**

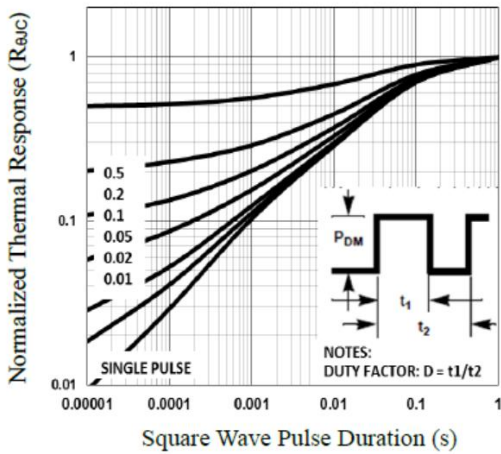
## Typical Performance Characteristics (Continue)



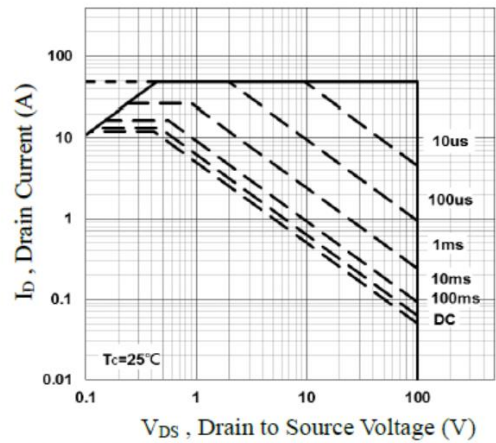
**Fig.7 Capacitance Characteristics**



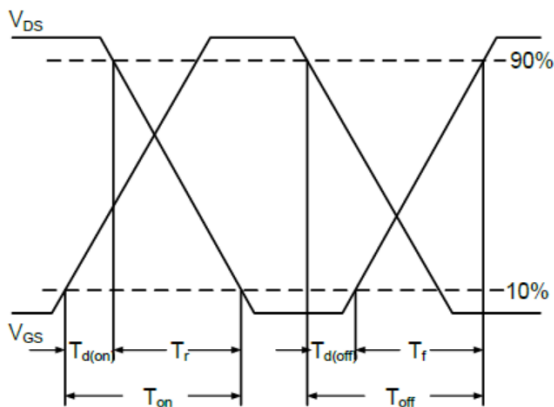
**Fig.8 Transfer Characteristics**



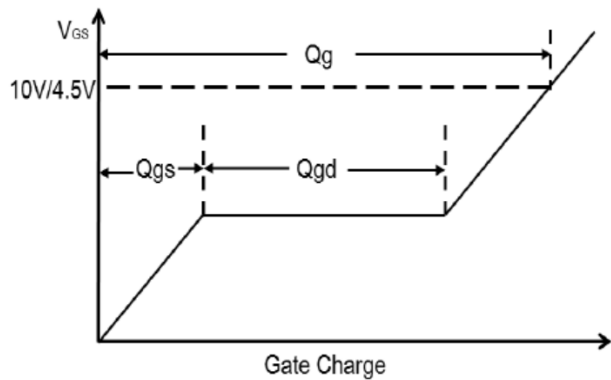
**Fig.9 Normalized Transient Impedance**



**Fig.10 Maximum Safe Operation Area**



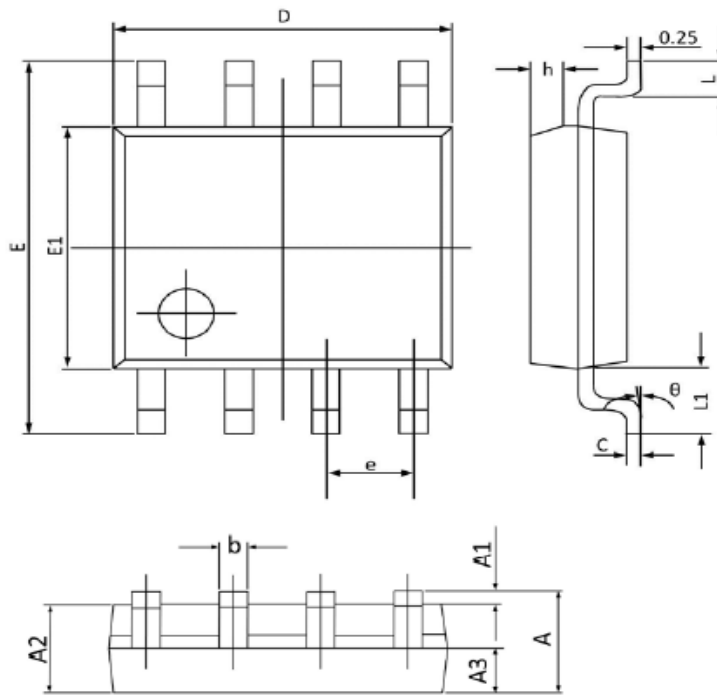
**Fig.11 Switching Time Waveform**



**Fig.12 Gate Charge Waveform**

## Package Dimension

### SOP-8









Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270 (BSC)		0.050 (BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050 (BSC)		0.041 (BSC)	
θ	0°	8°	0°	8°

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